MEG II 実験液体キセノン検出器用MPPCに対して 低温環境が与える影響の評価

Kohei Shimada
On behalf of MEG II collaboration
The University of Tokyo

Feb. 17th, 2020

Introduction

- The motivation of searching $\mu \to e \gamma$
- Overview of MEG II
- Liquid xenon photon detector

MPPC

- VUV-sensitive MPPC
- The mechanism of VUV detection
- MPPC PDE decrease
- Surface damage by VUV light

Measurement of PDE decrease

- Outline
- Setup
- Result
- Summary

Introduction

- The motivation of searching $\mu \to e \gamma$
- Overview of MEG II
- Liquid xenon photon detector

MPPC

- VUV-sensitive MPPC
- The mechanism of VUV detection
- MPPC PDE decrease
- Surface damage by VUV light

Measurement of PDE decrease

- Outline
- Setup
- Result
- Summary

The motivation of searching $\mu \rightarrow e \gamma$

- Neutrino oscillation was discovered (1998)
 - →Shows that neutrinos have mass and mixing
- $\mu \rightarrow e \gamma$ in the standard model

$$Br(\mu \to e\gamma) = \frac{3\alpha}{32\pi} \left| \sum_{i=2,3} U_{\mu i}^* U_{ei} \frac{\Delta m_{i1}^2}{M_W^2} \right|^2 \simeq 10^{-54}$$

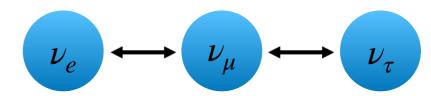
→Cannot be observed

- $\mu \rightarrow e \gamma$ in a new physics e.g. SUSY GUT
 - →Assume unknown heavy paticle

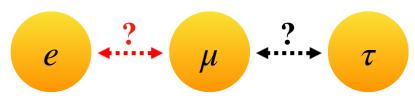
$$Br(\mu \to e\gamma) = \mathcal{O}(10^{-12}) - \mathcal{O}(10^{-14})$$

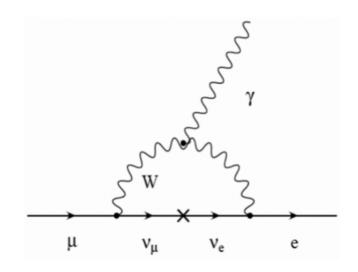
 \rightarrow Can be observed

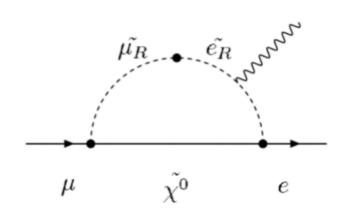
Neutrino



Charged lepton







Overview of the MEG II experiment at Paul Scherrer Institut

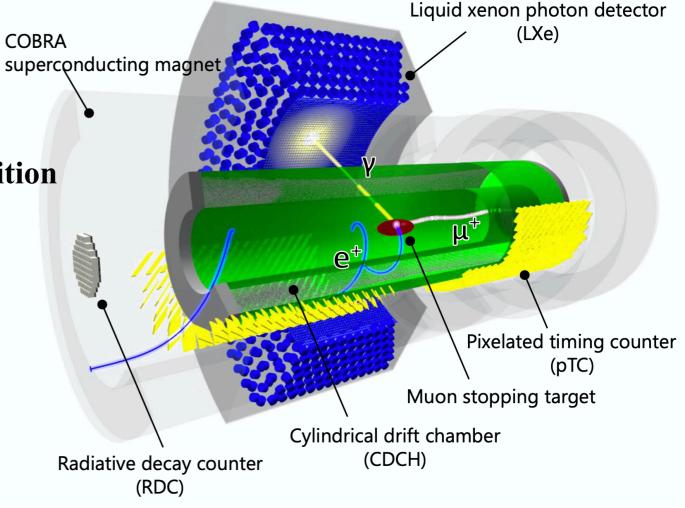


- The world's most intense μ beam $7 \times 10^7 \mu/\text{sec}$
- Muons are stopped at the target
- Two-body decay

• The photon energy, interaction point position

and time are measured by LXe





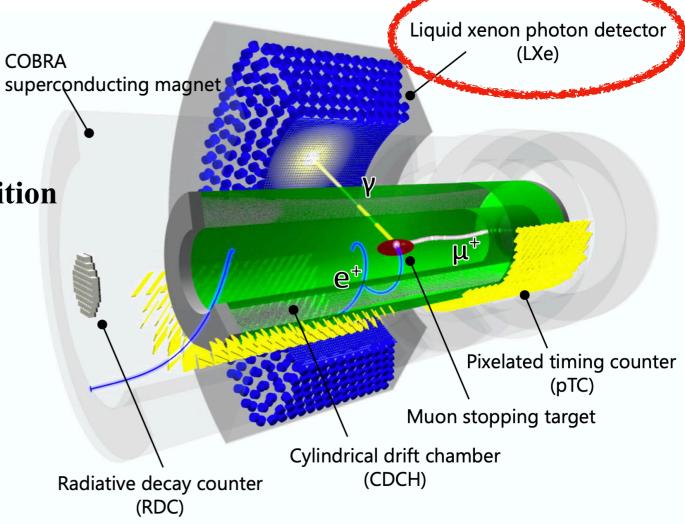
Overview of the MEG II experiment at Paul Scherrer Institut



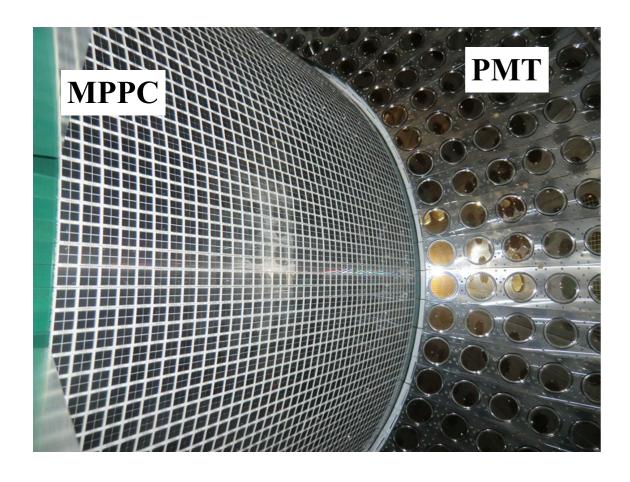
- The world's most intense μ beam $7 \times 10^7 \mu/\text{sec}$
- Muons are stopped at the target
- Two-body decay

• The photon energy, interaction point position and time are measured by LXe



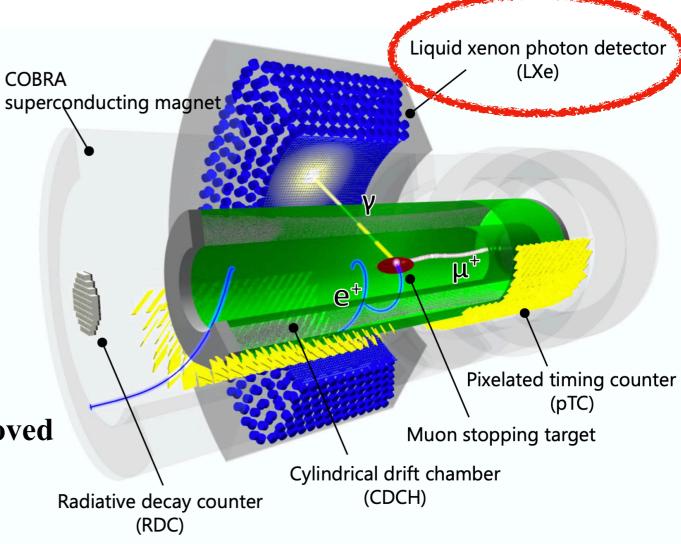


Liquid xenon photon detector (LXe)

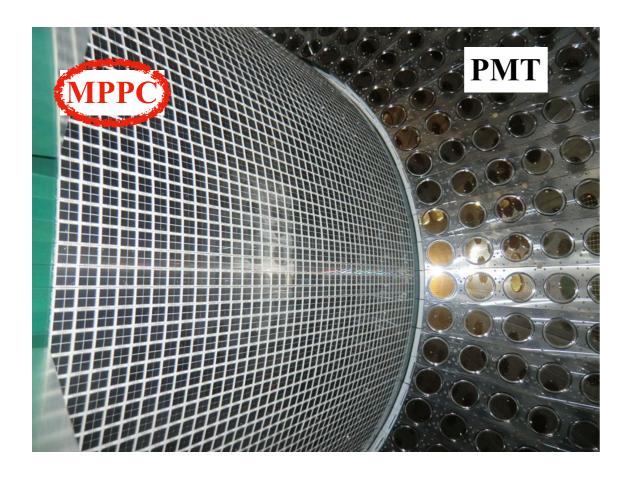




- Liquid xenon to measure 52.8MeV photon
- Detect the scintillation ($\lambda = 175$ nm)
- 4092 MPPCs, 668PMTs at 165K
- Energy and position resolutions will be improved as compared with MEG by a factor of two
- Under commissioning since 2017

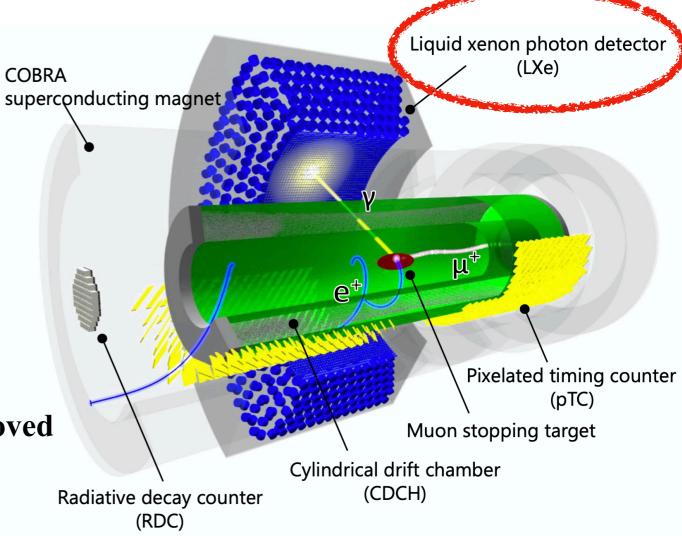


Liquid xenon photon detector (LXe)





- Liquid xenon to measure 52.8MeV photon
- Detect the scintillation ($\lambda = 175$ nm)
- 4092 MPPC, 668PMTs at 165K
- Energy and position resolutions will be improved as compared with MEG by a factor of two
- Under commissioning since 2017



Introduction

- The motivation of searching $\mu \to e \gamma$
- Overview of MEG II
- Liquid xenon photon detector

MPPC

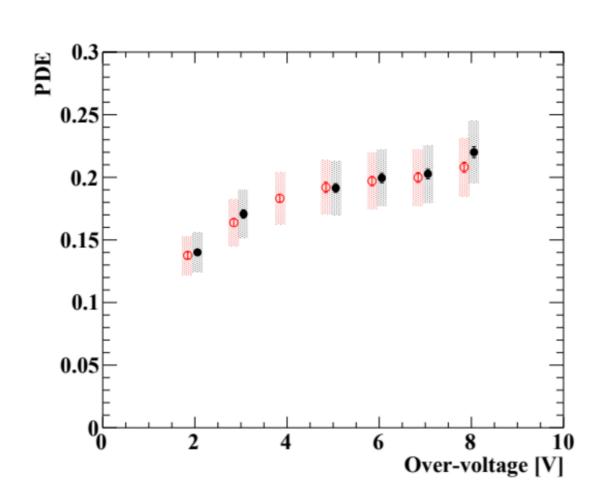
- VUV-sensitive MPPC
- The mechanism of VUV detection
- MPPC PDE decrease
- Surface damage by VUV light

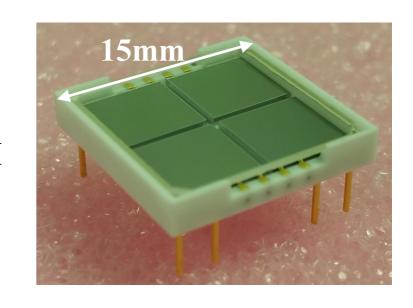
Measurement of PDE decrease

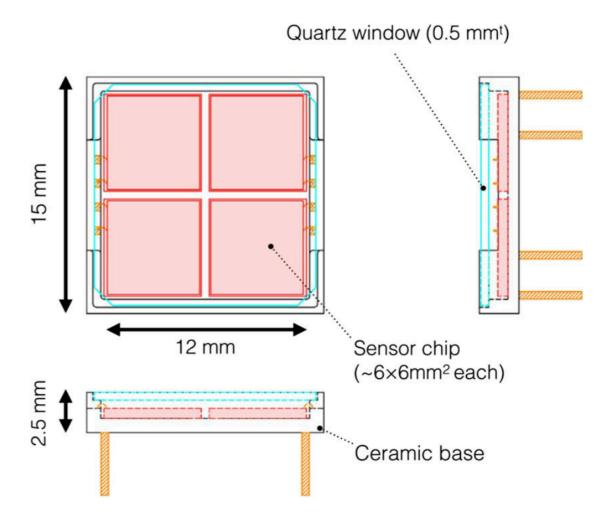
- Outline
- Setup
- Result
- Summary

VUV-sensitive MPPC (SiPM)

- SiPM is a high-performance photon detector
- VUV-sensitive MPPC has been newly developed for MEG II
- Operational at low temperature (165K)
- Photon detection efficiency (PDE) >15% at $\lambda = 175 \text{nm}$
- Large sensitive area $(12 \times 12 \text{ mm}^2)$



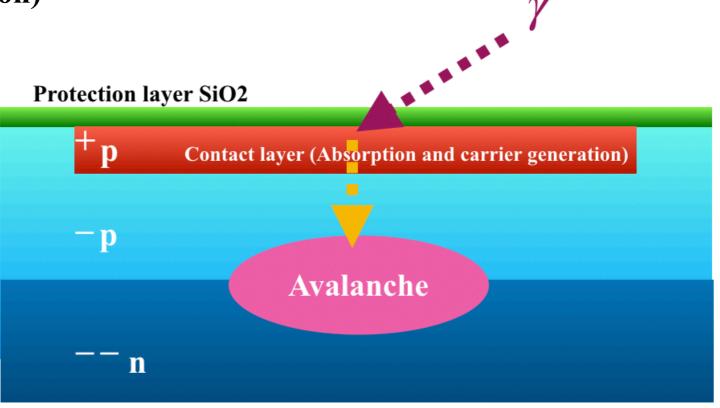




The mechanism of photon detection

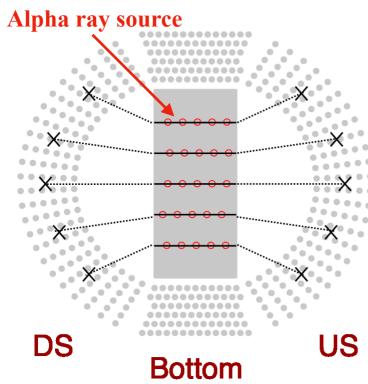
- General SiPM
- Depletion layer: p-n junction
- Incoming photons generate electron-hole pairs
- Reverse voltage is larger than a threshold
 - →"Geiger mode"
- · In geiger mode, carriers make other carriers
 - →Number of electron-hole pairs increase exponentially (avalanche multiplication) to make a signal
- Insensitive to VUV
 - →VUV stops near the surface
 - →Visible light reach the deep part

- VUV-sensitive MPPC
 - Remove the protection coating (epoxy)
 - Thin down the contact layer



VUV-sensitive MPPC PDE decrease

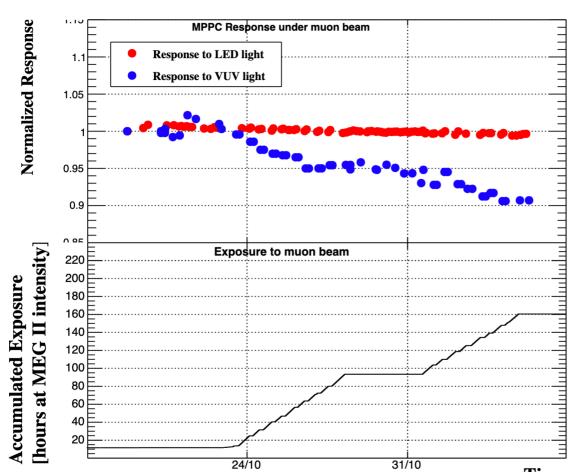
Top



- Alpha ray sources are in the detector
 - → Produce VUV scintillation light

• PDE =
$$\frac{\text{N(photon)}_{\text{observed}}}{\text{N(photon)}_{\text{expected}}} \sim 8\%$$

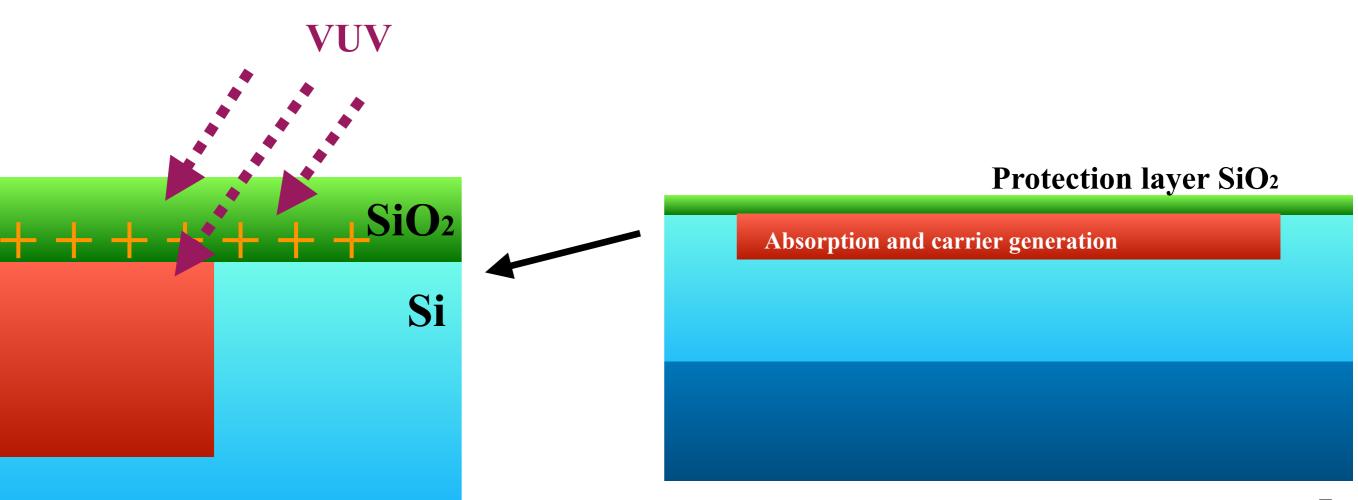
 \rightarrow much lower than that measured in Lab(>15%)



- Degradation of MPPC VUV-sensitivity
 - \rightarrow quite fast \sim 0.05%/hour (under MEG II beam intensity $7 \times 10^7 \mu/\text{sec}$)
- MEG II DAQ time (design): 140 days/year, 3 years
 - →This degradation is not negligible
- · A possible cause: Gamma, Neutron irradiation
 - →In lab test, no effect on PDE was observed (at room-temp)

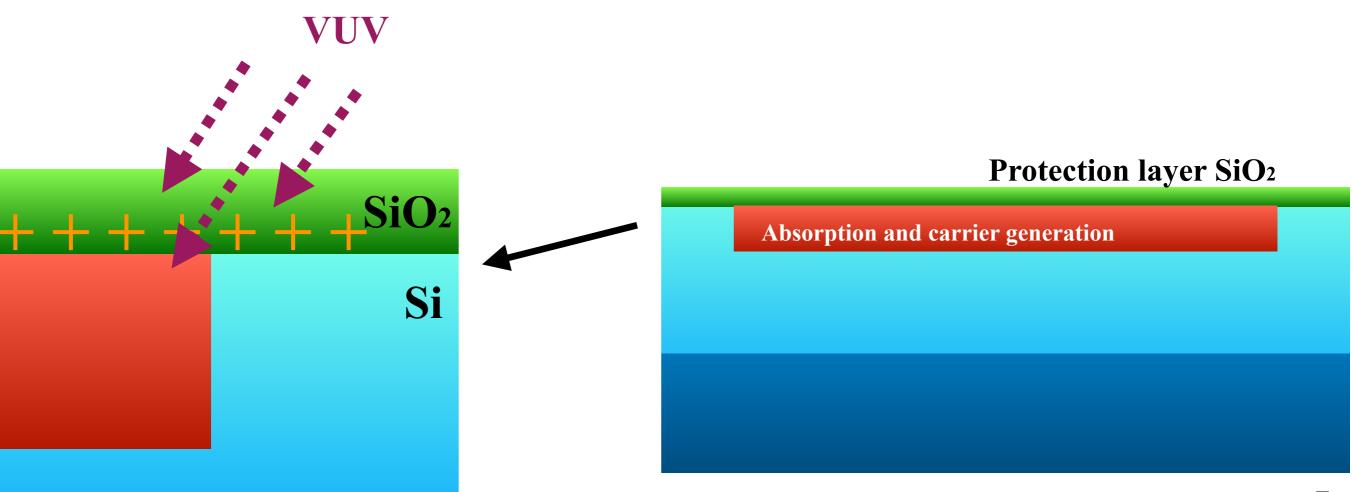
Surface damage by VUV light

- Electron-holes are generated in SiO2 by VUV light
- Holes are trapped at interface SiO₂-Si
- The electric field near the boundary of the two surfaces will be reduced by the holes
 - →Collection efficiency will be reduced
- Degradation seems accelerated at low temperature
 - →Holes hardly move



Surface damage by VUV light

- Electron-holes are generated in SiO2 by VUV light
- Holes are trapped at interface SiO₂-Si
- The electric field near the boundary of the two surfaces will be reduced by the holes
 - →Collection efficiency will be reduced
- Degradation seems accelerated at low temperature
 - →Holes hardly move



Introduction

- The motivation of searching $\mu \to e \gamma$
- Overview of MEG II
- Liquid xenon photon detector

MPPC

- VUV-sensitive MPPC
- The mechanism of VUV detection
- MPPC PDE decrease
- Surface damage by VUV light

Measurement of PDE decrease

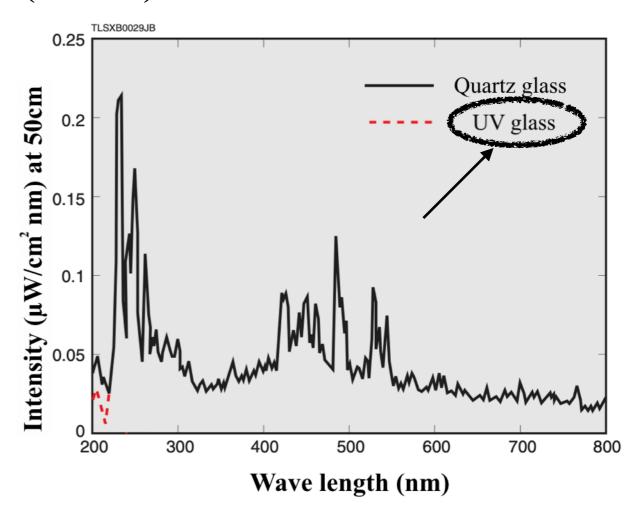
- Outline
- Setup
- Result
- Summary

Outline

- To survey the effect of low temperature on the PDE decrease
 - →Compare the PDE decrease at room temperature and low temperature
- To induce and monitor the PDE decrease
 - →Irradiate a MPPC
 - →Read current with no bias voltage

 (in previous research, correlation between current and PDE was observed)
- Xe flash lamp as a irradiation source
 - →To irradiate with short-wavelength light (~175nm)



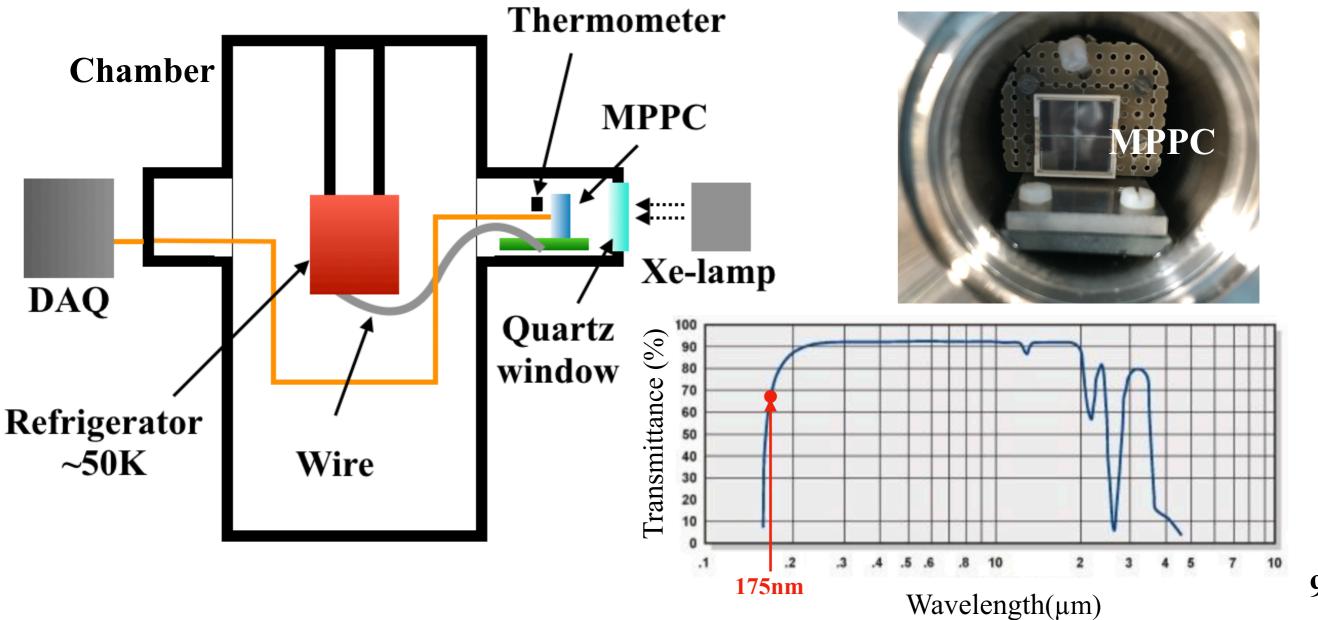


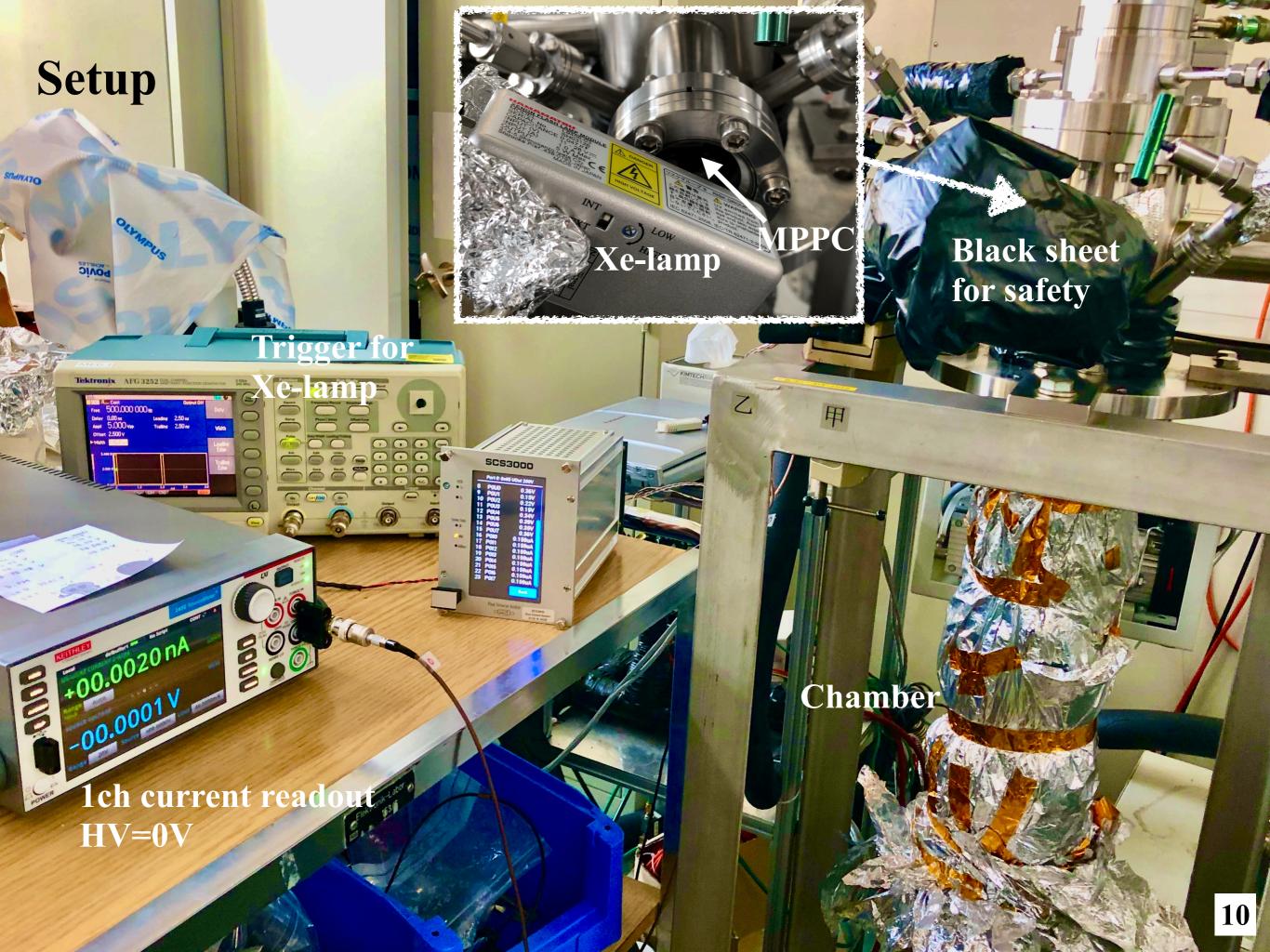
Setup

- Wire carries low temperature from refrigerator
- ~240K, around the MPPC
 - →Could not reach the LXe temp(165K)

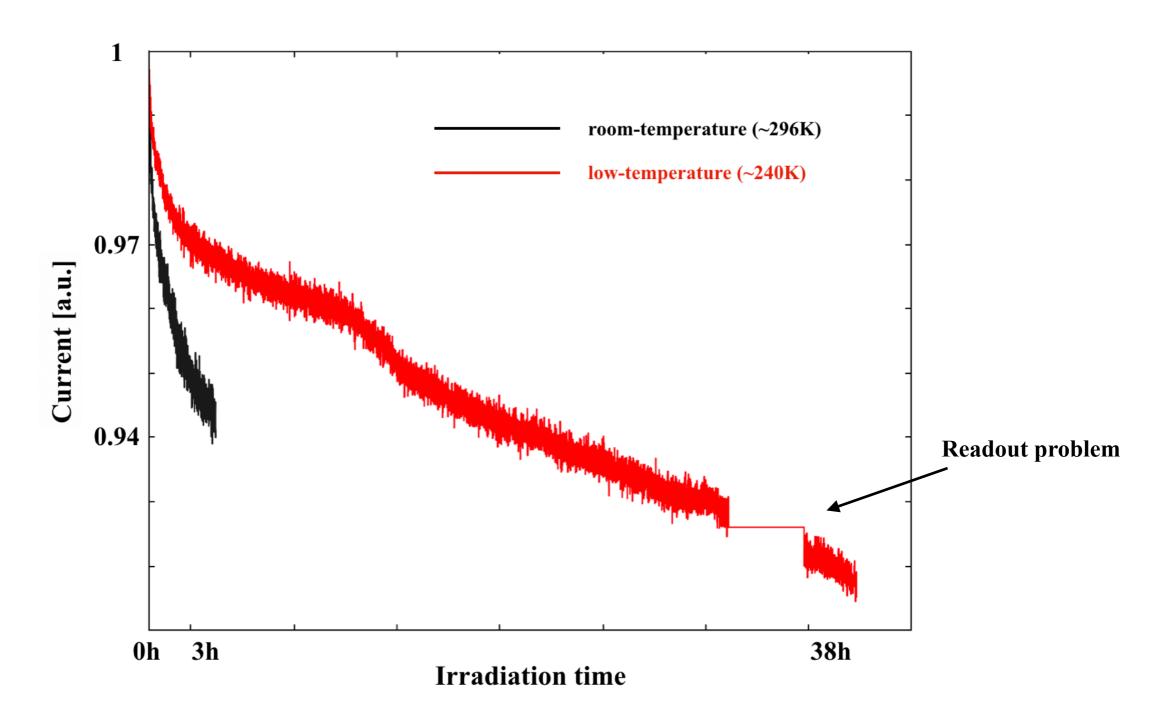
- Make vacuum in the chamber, for insulation MPPC is irradiated through quartz window
 - →Distance: 5cm
 - Read 1chip current (MPPC has 4chip)

$$\rightarrow$$
HV=0V



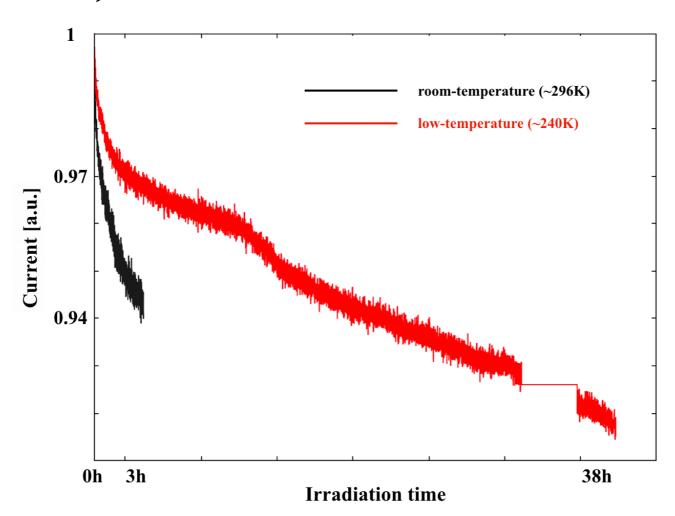


Result (HV=0V)



• Irradiated one MPPC (low-temp \rightarrow room-temp)

Result (HV=0V)



- Decrease of current was observed both at low-temp and room-temp
 - →This might means PDE decrease
- The decrease level of low-temperature is smaller than room-temperature
 - →Contrary to expectation
- The result includes the entire wavelength region
 - → Different from VUV irradiation
- The temp (~240K) is much higher than LXe temp (165K)

Summary

Motivation

PDE degradation of the MPPC was observed in LXe photon detector

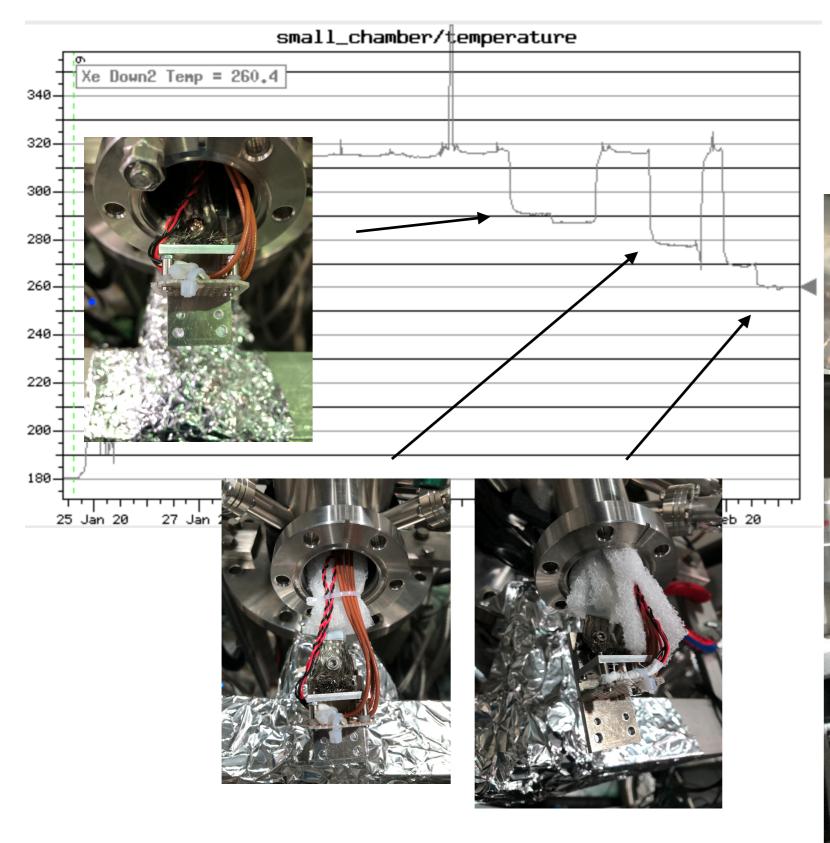
- PDE decrease by VUV irradiation at room-temp was slower than in LXe photon detector
 - → We measured at low-temp
- · Gamma, Neutron irradiation has no effect on PDE in previous research at room-temp
 - →Cannot exclude the possibility that the irradiation damage(Gamma, Neutron) at low-temp is different from room-temp

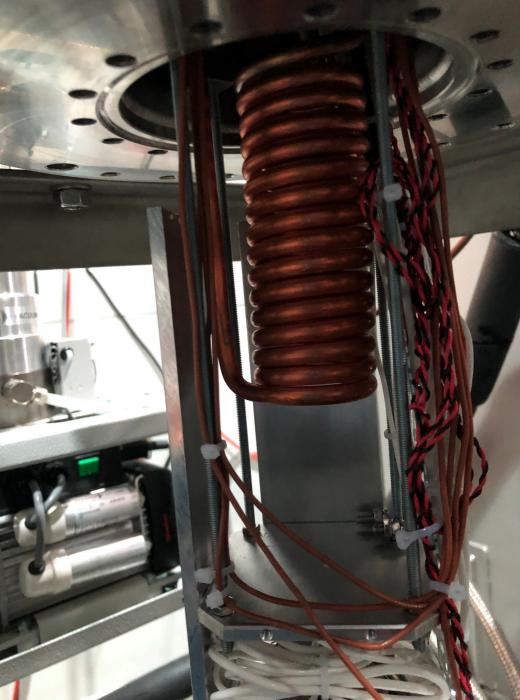
Measurement

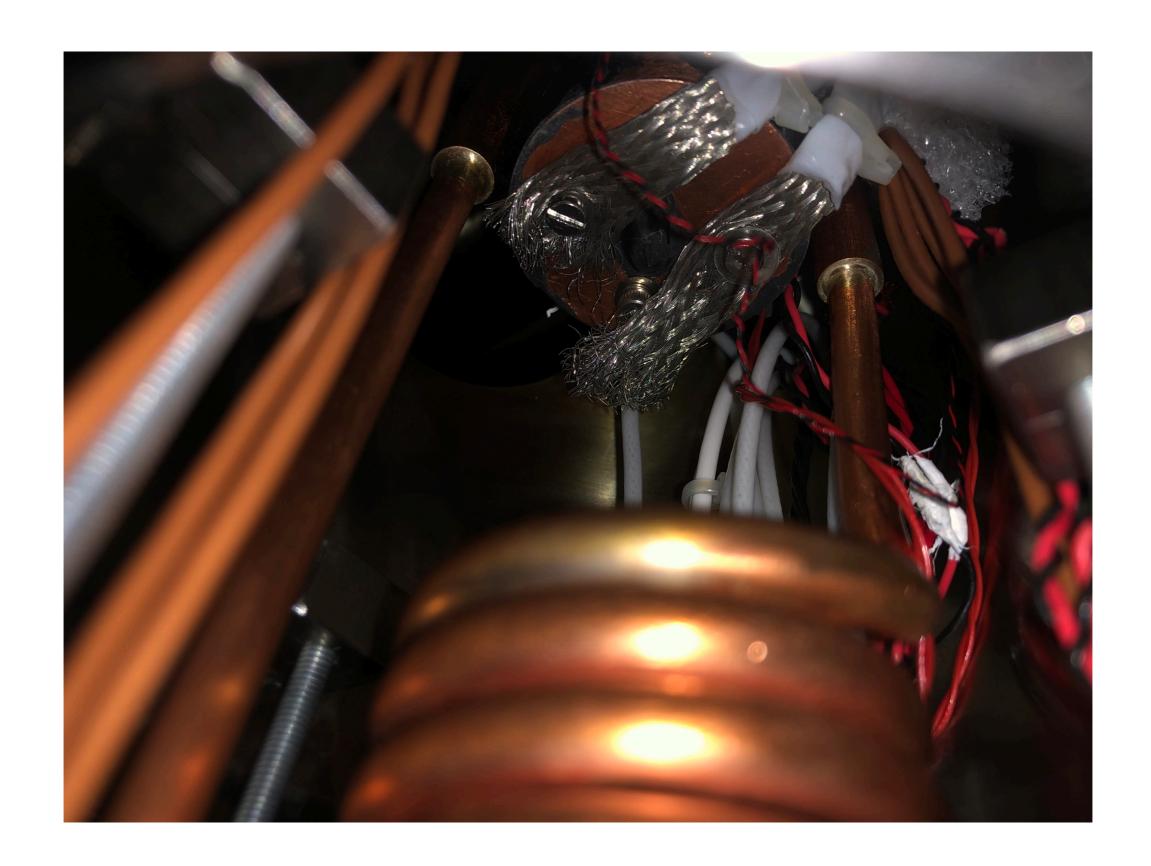
Room temp(~296K) vs Low temp(~240K)

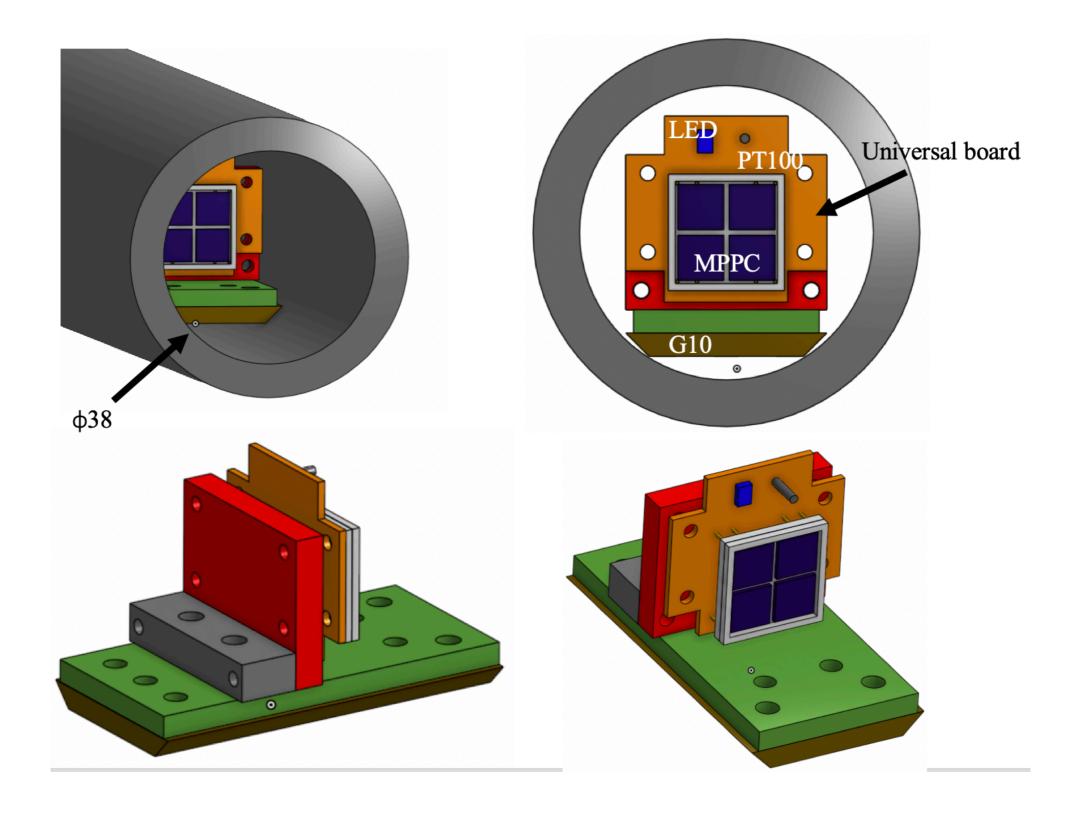
- Could not reach the LXe temp(165K)
 - →Improve the setup
- Contrary to expectations, current decrease at low temp was smaller
 - →We do not know the reason
 - →The possibility that we did not measure the PDE decrease for VUV light (Xe-lamp has other wave length)
 - →We should measure the charge for VUV light using filters

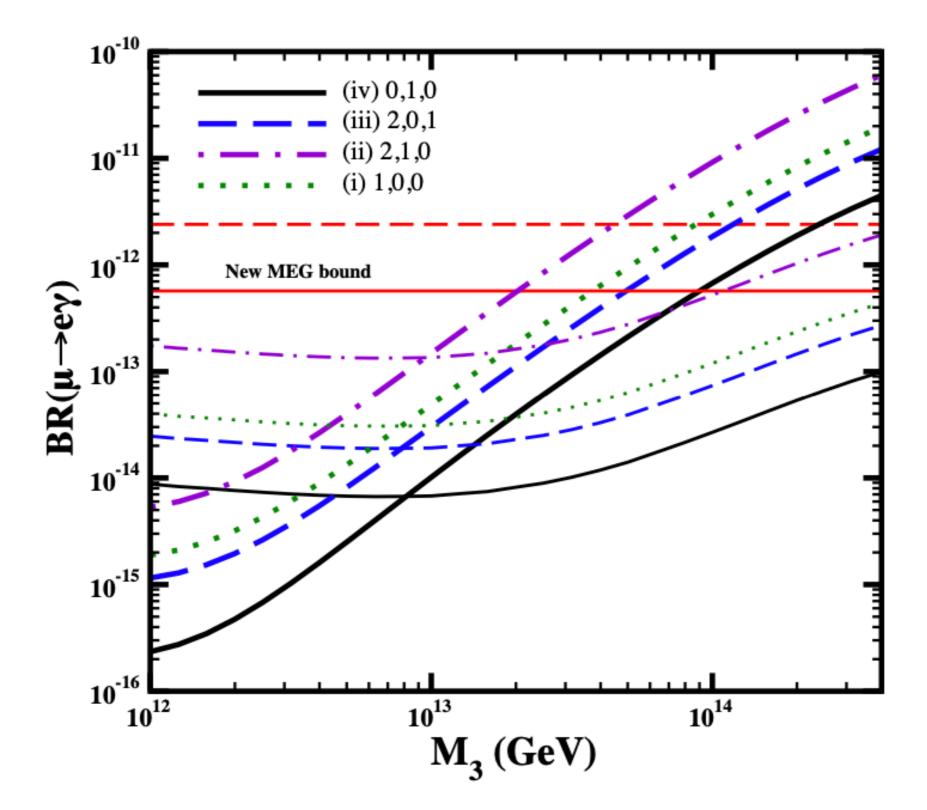
Backup slides



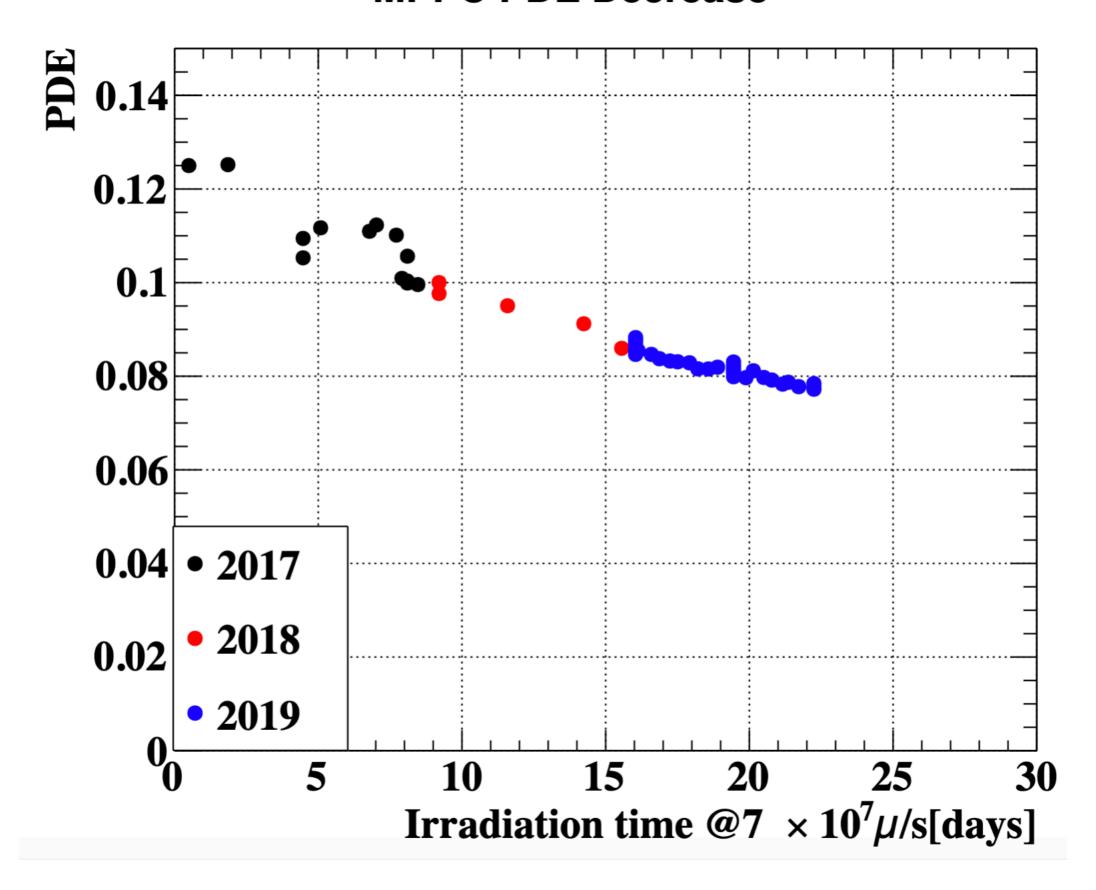








MPPC PDE Decrease





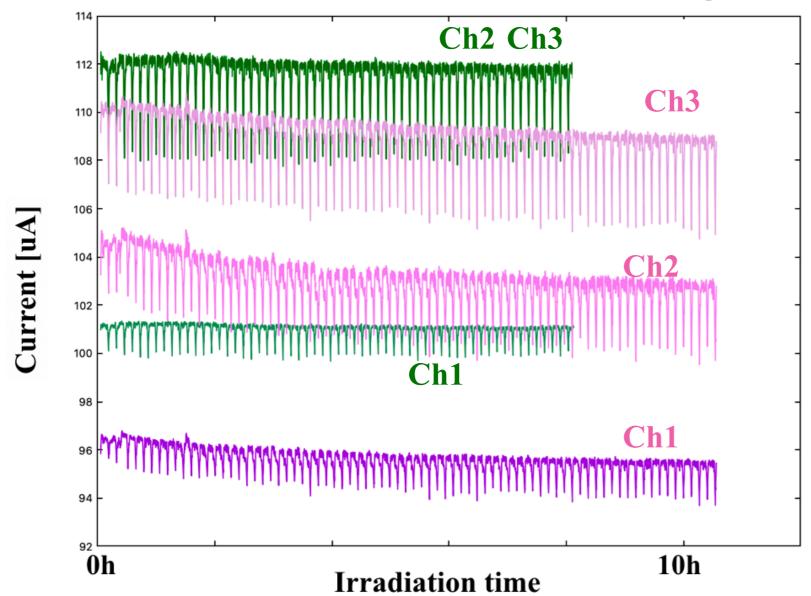
VUV Detection MPPC

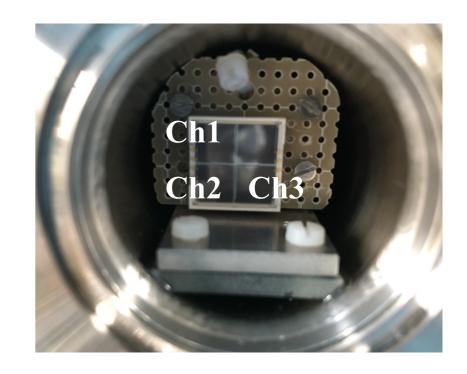
Protection layer (reflection) **VUV photons** Absorption and Carrier generation Cross section of the MPPC cell Avalanche

- For VUV light detection, precise control of MPPC's protection layer and absorption region is required.
- Generated photo-electrons excited by VUV light are transported to avalanche region by electric field. To obtain higher carrier collect efficiency, defect-less device is required.

room-temperature (296K)

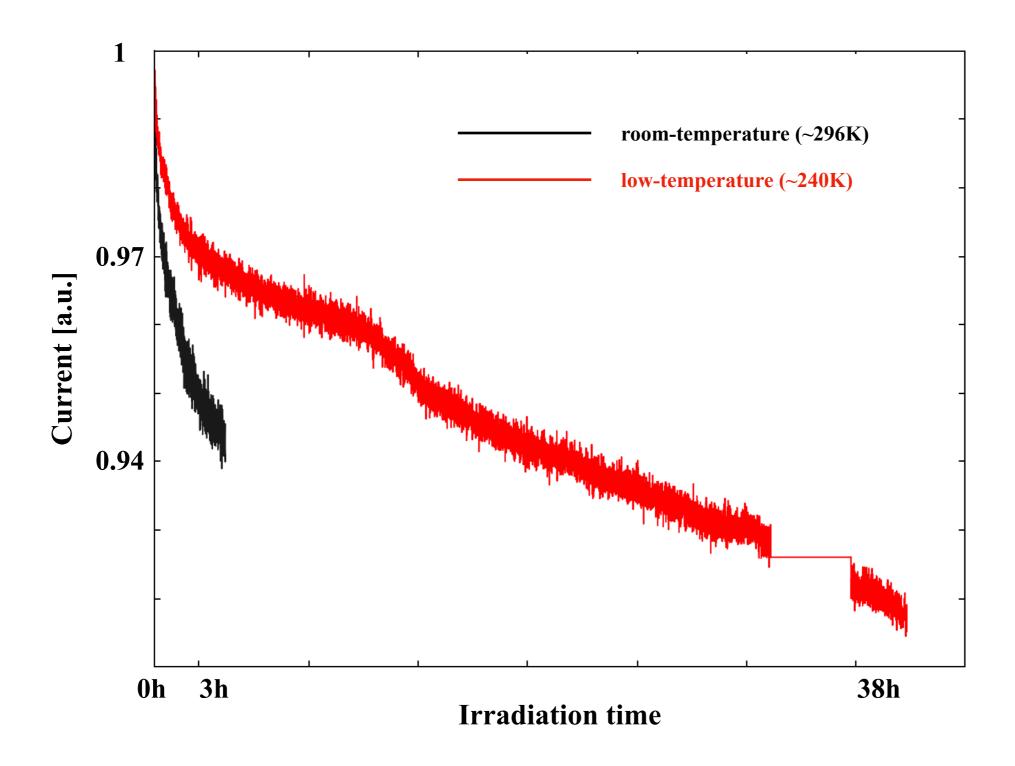
low-temperature (240K)

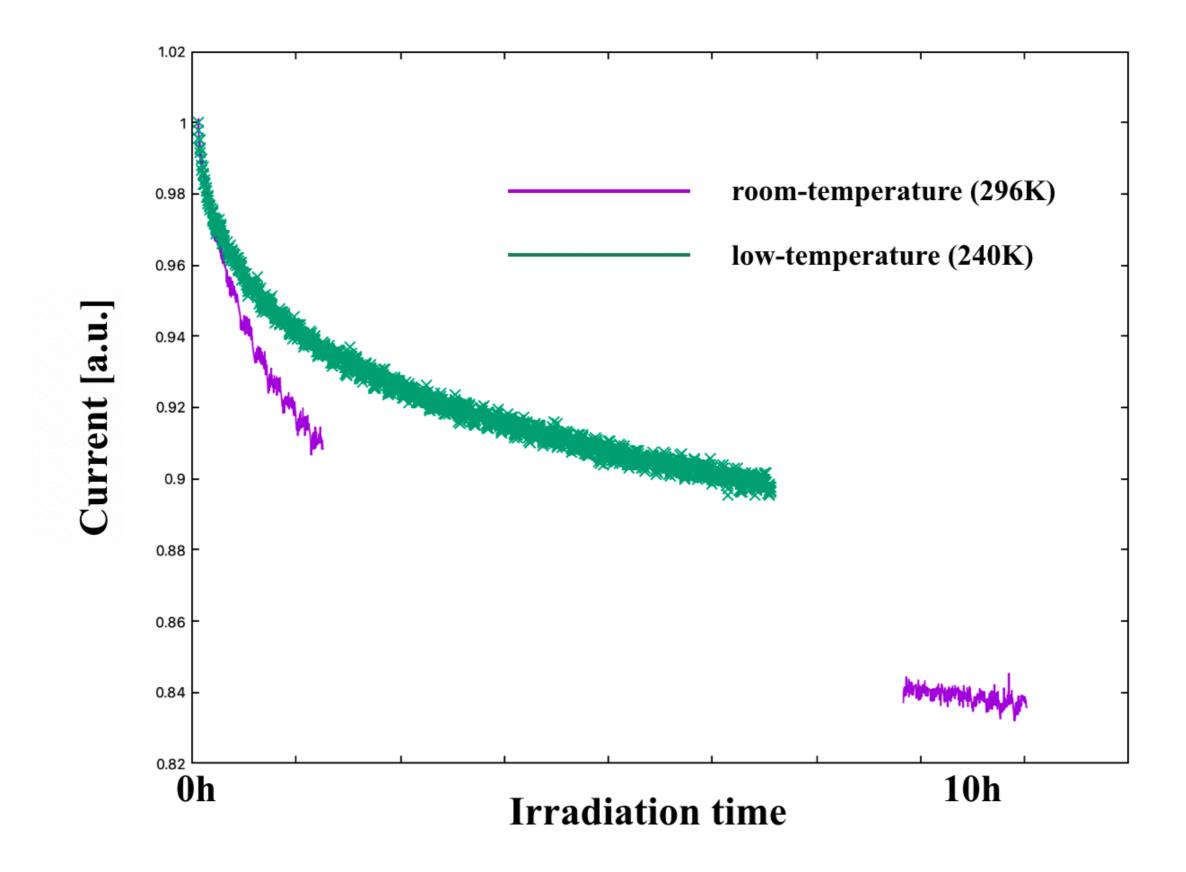




- 240K, around the MPPC
- Total irradiation time: ~10h
- · When bias voltage are supplied, low-temperature current seems to decrease

Result (HV=0V)





Possible Cause

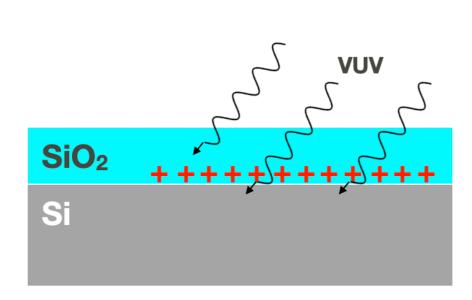
Surface damage by VUV-light

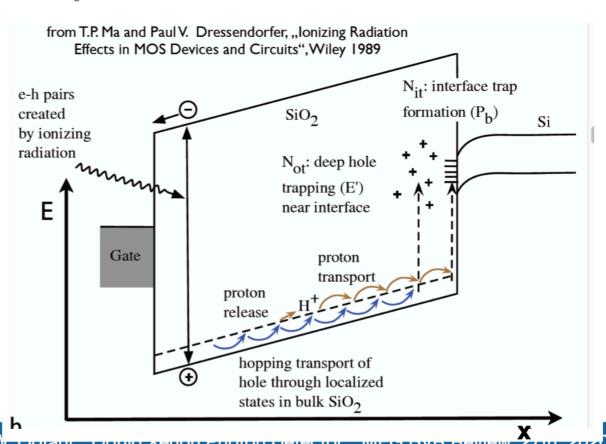
Electron-hole pair generated in SiO₂ by VUV light

- → Holes are trapped at interface SiO₂ Si
- → Accumulated positive charge will reduce electric field near Si surface, reducing collection efficiency of charge carrier
 - N.B. charge carrier generated within 5nm at Si surface for VUV

Similar phenomena are known for UV photo diode

- Degradation happens only with much larger amount of light at room temp.
- Degradation seems accelerated at low temp.

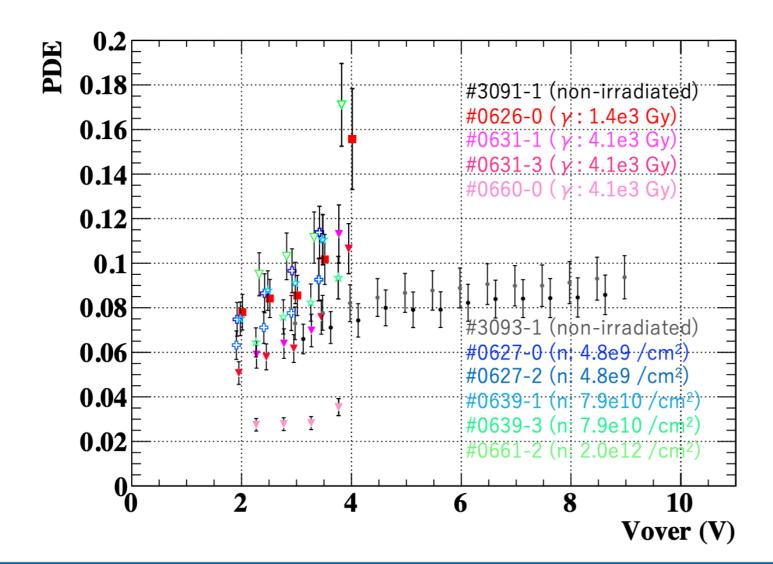




Highly Irradiated Samples

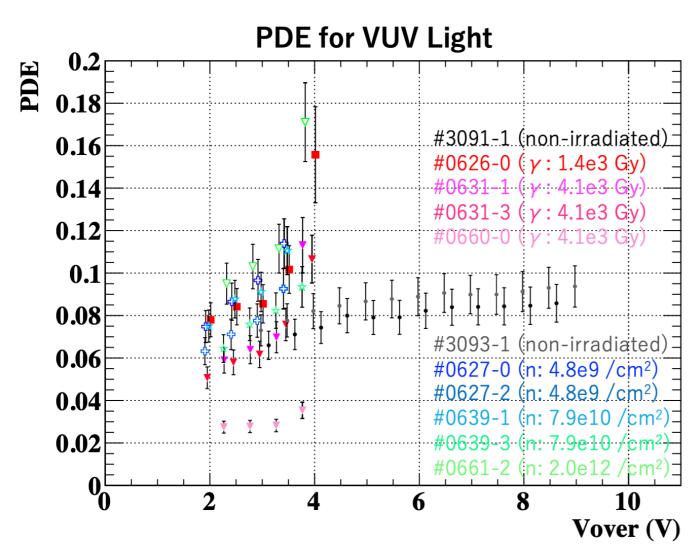
- Highly irradiated samples produced at irradiation facilities
- Tested in LXe

	Gamma [Gy]	Neutron [n _{1MeV} /cm ²]
Dose	(1.4-4.1)×10 ³	4.8×10 ⁹ - 2.0×10 ¹²
MEG II (3yrs)	~0.6	~108



→No effect on PDE!

PDE for VUV Light



- PDE degradation was not observed for all irradiated samples.
- Overall PDE were lower than those of the previous measurements (14-20%)
 purity of LXe??
- Only PDE of #0660-0 was lower though other samples with the same dose level were not the case.
 - PDE of #0660-0 for visible light was similar to others.
 - ← there might be a certain damage in the surface except for radiation damage.

XErrors include statistic errors and a systematic error of W value (10%)